

2SD1441

加急出货

Silicon NPN Triple-Diffused Junction Mesa Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- High breakdown voltage and high reliability by glass passivation
- High speed switching
- Wide area of safety operation (ASO)

■ Absolute Maximum Ratings (Tc=25°C)

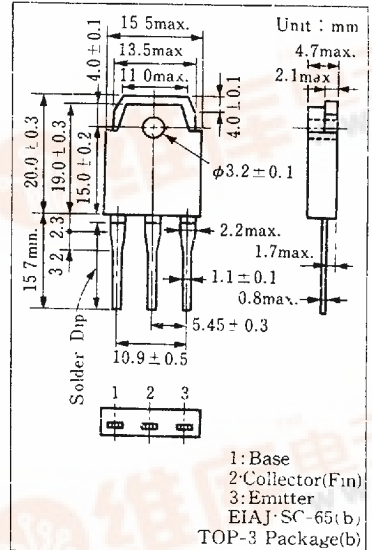
Item	Symbol	Value	Unit
Collector-base voltage	V_{CB0}	1500	V
Collector-emitter voltage	V_{CEs}	1500	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	4	A
Peak collector current	I_{CP}^*	15	A
Peak base current	I_{BP}	3.5	A
Reverse peak base current	I_{BP}	-2.5	A
Collector power dissipation	Tc=25°C	P_C	W
	Ta=25°C		
		2.5	
Junction temperature	T_j	130	°C
Storage temperature	T_{stg}	-55~+130	°C

* Non repetitive peak value

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=750V, I_F=0$			50	μA
		$V_{CB}=1500V, I_F=0$			1	mA
Emitter-base voltage	V_{EBO}	$I_E=500mA, I_C=0$	5			V
DC current gain	h_{FE}	$V_{CE}=10V, I_C=3A$	5		15	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=3A, I_B=1A$			1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=3A, I_B=1A$			1.5	V
Transition frequency	f_T	$V_{CE}=10V, I_C=0.5A, f=0.5MHz$		2		MHz
Fall time	t_f	$I_C=3A, I_{Bend}=1A$			0.75	μs
Storage time	t_{stg}	$L_{trab}=5\mu H$	4		9	μs
Diode forward voltage	V_F	$I_C=-4A, I_B=0$			-2.2	V

■ Package Dimensions



■ Inner Circuit

